

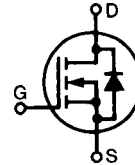
# HiPerFET™ MOSFET ISOPLUS220™

**Electrically Isolated Back Surface**

N-Channel Enhancement Mode  
High dv/dt, Low  $t_{rr}$ , HDMOS™ Family

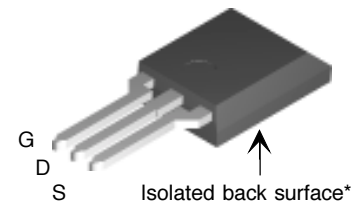
**IXFC 80N08**  
**IXFC 80N085**

$V_{DSS}$	$I_{D25}$	$R_{DS(on)}$
<b>80 V</b>	<b>80 A</b>	<b>9 mΩ</b>
<b>85 V</b>	<b>80 A</b>	<b>9 mΩ</b>



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	80N08	80 V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	80N085	85 V
$V_{GS}$	Continuous		$\pm 20$ V
$V_{GSM}$	Transient		$\pm 30$ V
$I_{D25}$	$T_C = 25^\circ\text{C}$		80 A
$I_{L(RMS)}$	Lead current limit		80 A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$		75 A
$I_{AR}$	$T_C = 25^\circ\text{C}$		320 A
$E_{AR}$	$T_C = 25^\circ\text{C}$		30 mJ
$E_{AS}$			1.0 J
dv/dt	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$		5 V/ns
$P_D$	$T_C = 25^\circ\text{C}$		230 W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s		300 $^\circ\text{C}$
$F_C$	Mounting force	11..65/2.4..11	Nm/lb
$V_{ISOL}$	50/60 Hz, RMS $t = 1$ minute leads-to-tab		2500 V~
Weight			2 g

## ISOPLUS220™



G = Gate, D = Drain,  
S = Source

\* Patent pending

## Features

- Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- Low drain to tab capacitance (<35pF)
- Low  $R_{DS(on)}$
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Fast intrinsic Rectifier

## Applications

- DC-DC converters
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control

## Advantages

- Easy assembly: no screws or isolation foils required
- Space savings
- High power density
- Low collector capacitance to ground (low EMI)

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$V_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	80N08 80 80N085 85		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4\text{ mA}$	2.0		4.0 V
$I_{GSS}$	$V_{GS} = \pm 20\text{ V}_{DC}$ , $V_{DS} = 0$			$\pm 100\text{ nA}$
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0\text{ V}$	$T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		50 $\mu\text{A}$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = I_T$ Notes 1, 2			9 mΩ

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}$ ; $I_D = I_T$ Notes 1, 2	35	55	S
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		4800	pF
$C_{oss}$			1675	pF
$C_{rss}$			590	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = 0.5 I_{D25}$ , $R_G = 2.5\ \Omega$ (External)		50	ns
$t_r$			75	ns
$t_{d(off)}$			95	ns
$t_f$			31	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = I_T$ Notes 2		180	nC
$Q_{gs}$			42	nC
$Q_{gd}$			75	nC
$R_{thJC}$			0.54	K/W
$R_{thCK}$		0.25		K/W

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_S$	$V_{GS} = 0\text{ V}$			80 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			320 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{ V}$ , Note 1			1.5 V
$t_{rr}$	$I_F = 25\text{ A}$ $-di/dt = 100\text{ A}/\mu\text{s}$ , $V_R = 50\text{ V}$			200 ns
$Q_{RM}$			0.5	$\mu\text{C}$
$I_{RM}$			6	A

Note: 1. Pulse test,  $t \leq 300\ \mu\text{s}$ , duty cycle  $d \leq 2\%$   
 2.  $I_T = 40\text{ A}$

**ISOPLUS220 OUTLINE**

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55 BASIC	
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
L4	.039	.059	1.00	1.50
T*			42.5°	47.5°

Note: All terminals are solder plated.  
 1 - Gate  
 2 - Drain  
 3 - Source

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025